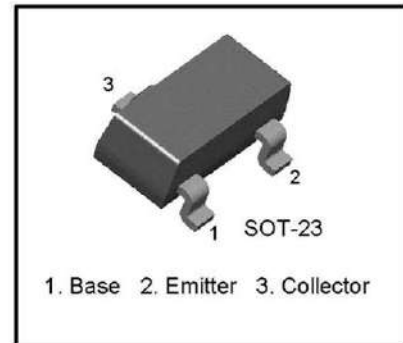


- **Low Frequency Power Amplifier**

- Complement to KSC2859



PNP Epitaxial Silicon Transistor

- **Absolute Maximum Ratings** $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{CBO}	Collector-Base Voltage	-35	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-500	mA
P_C	Collector Power Dissipation	150	mW
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	-55 ~ 150	$^\circ\text{C}$

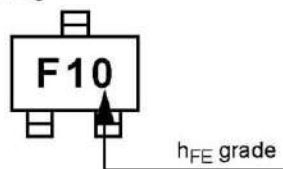
- **Electrical Characteristics** $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
I_{CBO}	Collector Cut-off Current	$V_{CB} = -35\text{V}, I_E = 0$			-0.1	μA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	μA
h_{FE1}	DC Current Gain	$V_{CE} = -1\text{V}, I_C = -100\text{mA}$	70		240	
h_{FE2}		$V_{CE} = -6\text{V}, I_C = -400\text{mA}$	25			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -100\text{mA}, I_B = -10\text{mA}$		-0.1	-0.25	V
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = -1\text{V}, I_C = -100\text{mA}$		-0.8	-1.0	V
f_T	Current Gain Bandwidth Product	$V_{CE} = -6\text{V}, I_C = -20\text{mA}$		200		MHz
C_{ob}	Output Capacitance	$V_{CB} = -6\text{V}, I_E = 0, f = 1\text{MHz}$		13		pF

- **h_{FE} Classification**

Classification	O	Y
h_{FE1}	70 ~ 140	120 ~ 240

Marking



Typical Characteristics

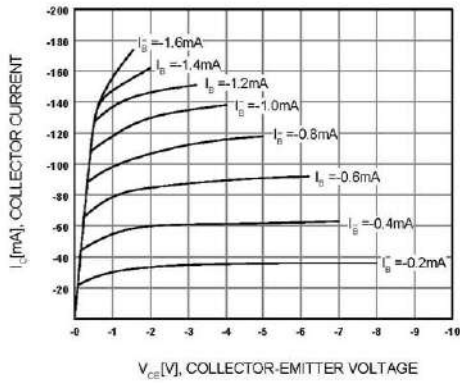


Figure 1. Static Characteristic

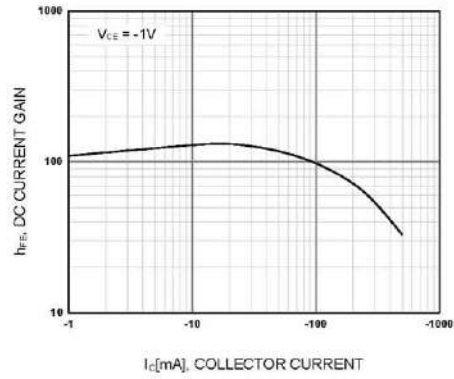


Figure 2. DC current Gain



Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

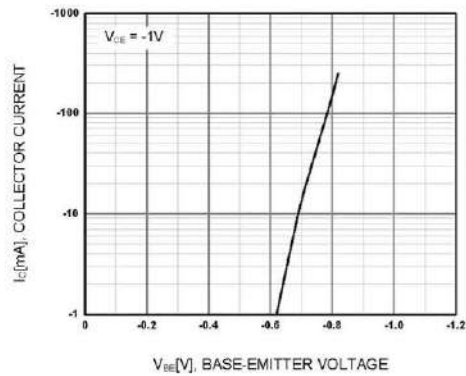


Figure 4. Base-Emitter On Voltage

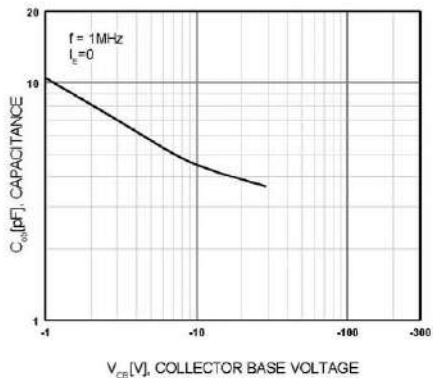


Figure 5. Collector Output Capacitance

KSA1182

Package Dimensions

SOT-23

